

In the Claims

Please amend the claims as indicated below.

C1 38. (Amended) A method of forming a capacitor including:  
forming a first electrode selected from a group consisting of transition metals, conductive metal-oxides, alloys thereof, and combinations thereof;  
forming a dielectric on the first electrode and an uppermost surface of a substrate assembly; and  
forming a second electrode on the dielectric and the uppermost surface of the substrate assembly.

49. (Amended) The method of claim 38, further comprising forming the substrate assembly before forming the first electrode.

C3 51. (Twice Amended) The method of claim 38, wherein forming the first electrode includes:  
forming a layer of hemispherical grain on the substrate assembly; and  
forming the first electrode on the hemispherical grain polysilicon.

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52. (Amended) A method of forming a capacitor, comprising:  
forming a layer of hemispherical grain polysilicon;  
forming a first electrode on the hemispherical grain polysilicon, wherein the first electrode is selected from a group consisting of transition metals, conductive metal-oxides, alloys thereof, and combinations thereof;  
forming a dielectric on the first electrode and an uppermost surface of a substrate assembly; and  
forming a second electrode on the dielectric and the uppermost surface of the substrate assembly.

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57. (Amended) The method of claim 52, further comprising forming the substrate assembly before forming the first electrode.

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58. (Amended) A method, comprising:  
forming a substrate assembly;  
forming a layer of hemispherical grain polysilicon on the substrate assembly;  
forming a first electrode on the hemispherical grain polysilicon, wherein the first electrode is selected from a group consisting of transition metals, conductive metal-oxides, alloys thereof, and combinations thereof;  
removing a portion of the substrate assembly;  
removing the hemispherical grain polysilicon;